

Description

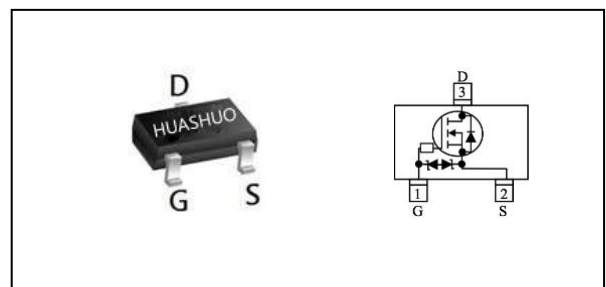
The HSSC3134 is the high cell density trenched N-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications. The HSSC3134 meets the RoHS and Green Product requirement with full function reliability approved.

- Fast Switching Speed
- Super Low Gate Charge
- High-Side Switching
- Low Threshold

Product Summary

V_{DS}	20	V
$R_{DS(ON),max}$	370	m Ω
I_D	0.77	A

SOT723 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D@T_A=25^\circ C$	Continuous Drain Current, V_{GS} @ 4.5V ₁	0.77	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, V_{GS} @ 4.5V ₁	0.5	A
I_{DM}	Pulsed Drain Current ₂	1.9	A
$P_D@T_A=25^\circ C$	Total Power Dissipation ₃	0.15	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ₁	---	890	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ₁	---	500	$^\circ C/W$



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	20	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =4.5V, I _D =650mA	---	---	370	mΩ
		V _{GS} =2.5V, I _D =550mA	---	---	440	
		V _{GS} =1.8V, I _D =450mA	---	---	750	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	0.35	---	1.1	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =20V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =20V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±10V, V _{DS} =0V	---	---	±20	uA
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =800mA	1	---	---	S
Q _g	Total Gate Charge (4.5V)	V _{DS} =10V, V _{GS} =4.5V, I _D =550mA	---	1.1	---	nC
Q _{gs}	Gate-Source Charge		---	0.14	---	
Q _{gd}	Gate-Drain Charge		---	0.22	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =10V, V _{GS} =4.5V, R _G =10Ω I _D =500mA	---	6.6	---	ns
T _r	Rise Time		---	4.5	---	
T _{d(off)}	Turn-Off Delay Time		---	17	---	
T _f	Fall Time		---	6.8	---	
C _{iss}	Input Capacitance	V _{DS} =16V, V _{GS} =0V, f=1MHz	---	60	---	pF
C _{oss}	Output Capacitance		---	15	---	
C _{rss}	Reverse Transfer Capacitance		---	11	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	0.77	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

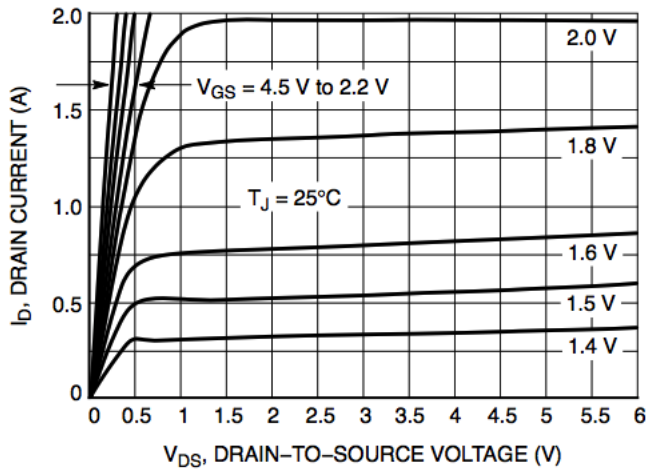


Figure 1. On-Region Characteristics

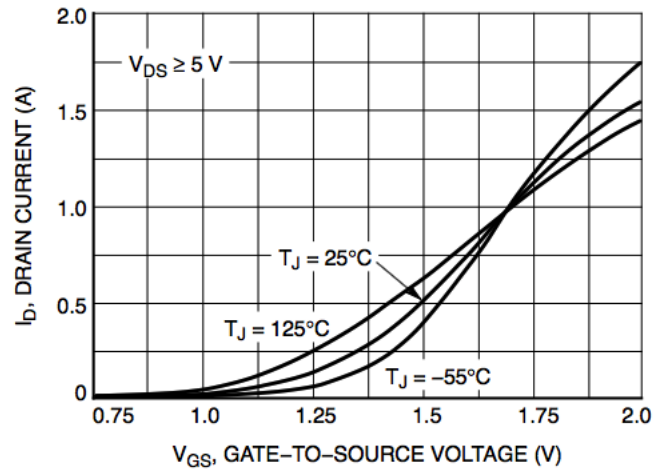


Figure 2. Transfer Characteristics

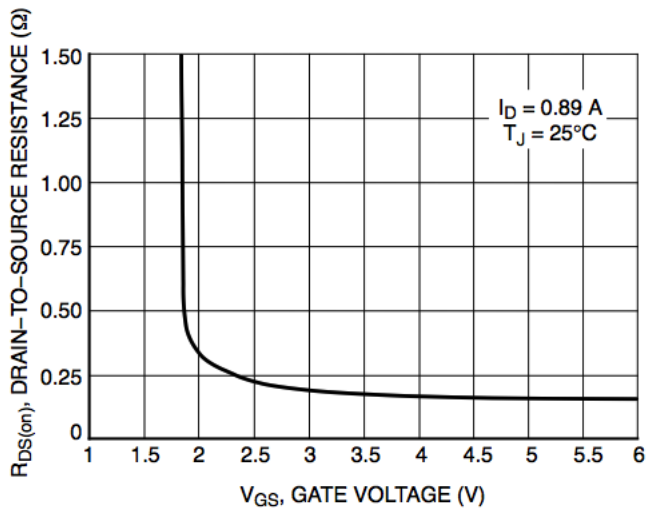


Figure 3. On-Resistance vs. Gate-to-Source Voltage

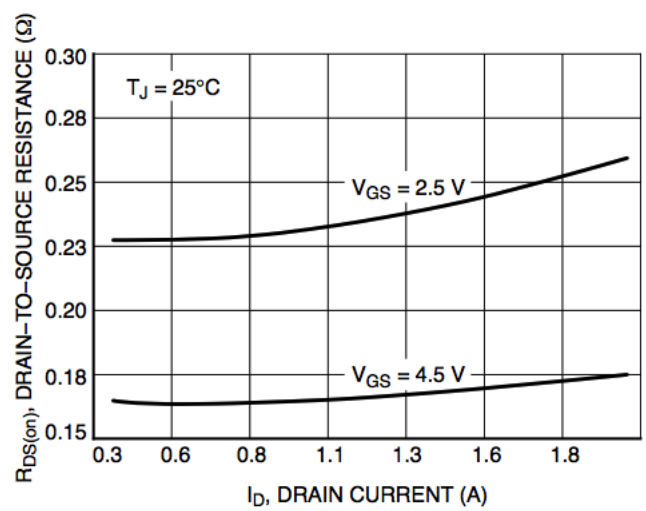


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

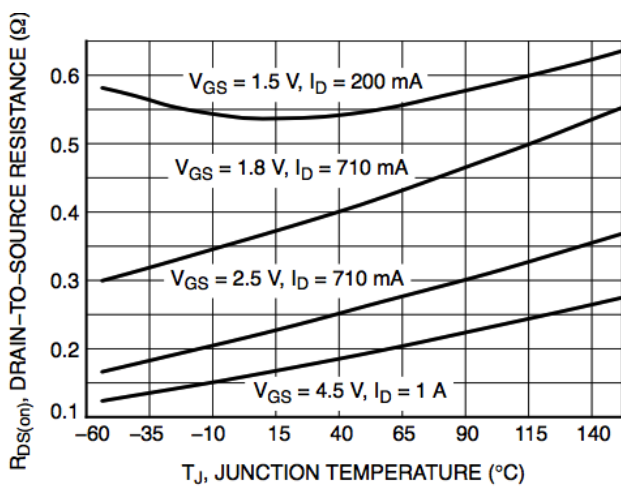


Figure 5. On-Resistance Variation with Temperature

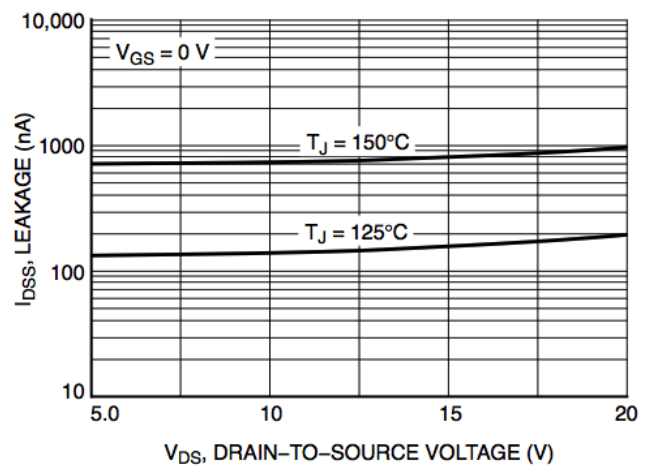


Figure 6. Drain-to-Source Leakage Current vs. Voltage



N-Ch 20V Fast Switching MOSFETs

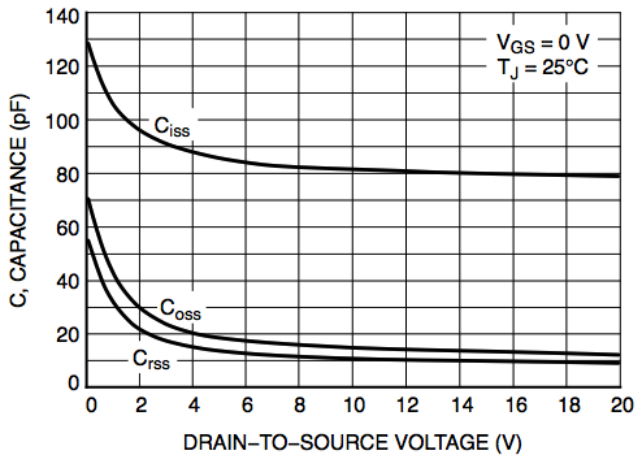


Figure 7. Capacitance Variation

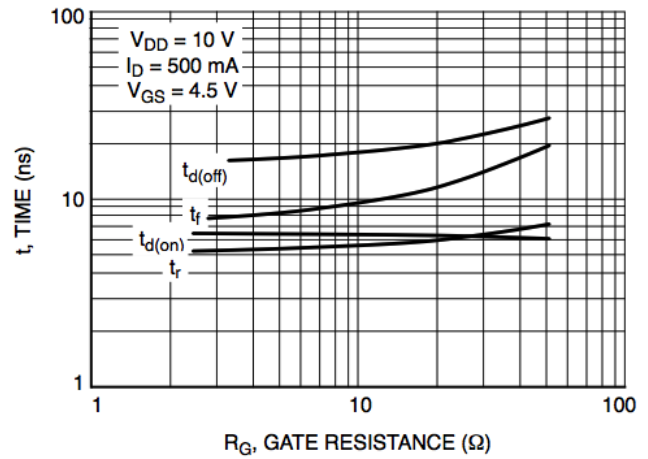


Figure 8. Resistive Switching Time Variation vs. Gate Resistance

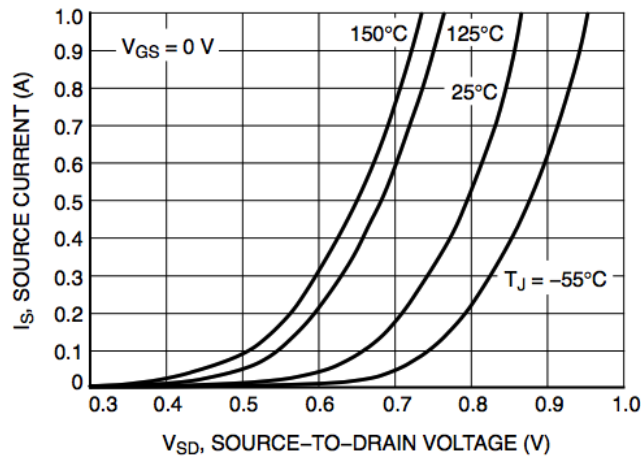
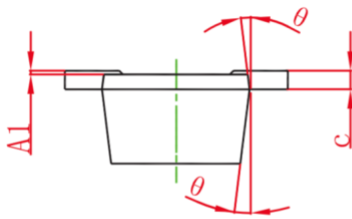
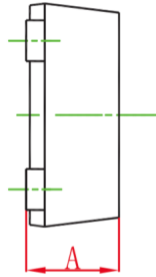
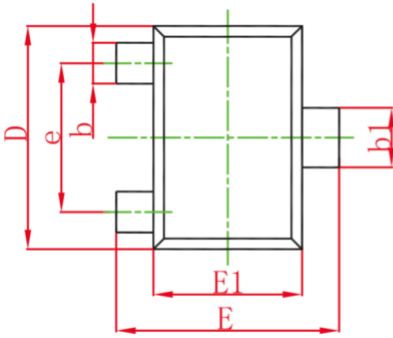


Figure 9. Diode Forward Voltage vs. Current



Ordering Information

Part Number	Package code	Packaging
HSSC3134	SOT-723	8000/Tape&Reel



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.430	0.500	0.017	0.020
A1	0.000	0.050	0.000	0.002
b	0.170	0.270	0.007	0.011
b1	0.270	0.370	0.011	0.015
c	0.080	0.150	0.003	0.006
D	1.150	1.250	0.045	0.049
E	1.150	1.250	0.045	0.049
E1	0.750	0.850	0.030	0.033
e	0.800TYP.		0.031TYP.	
θ	7° REF.		7° REF.	

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